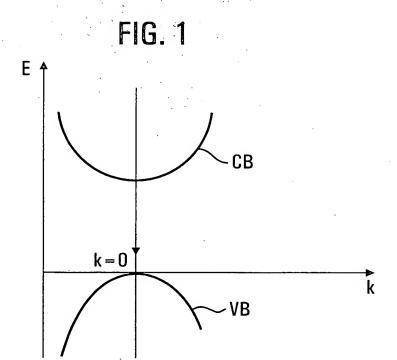
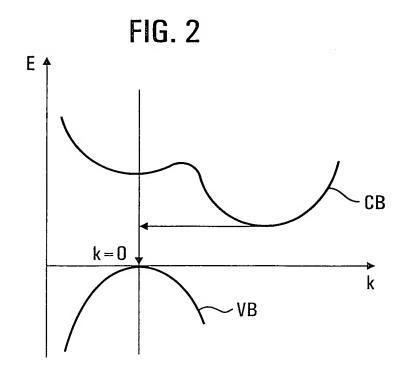
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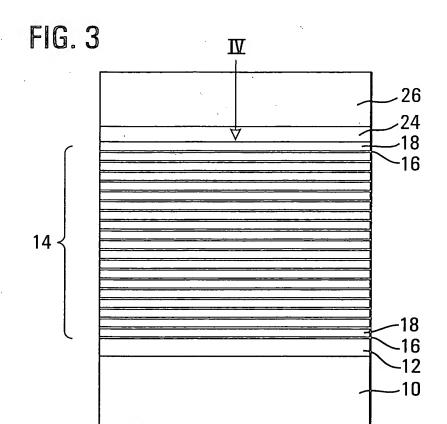


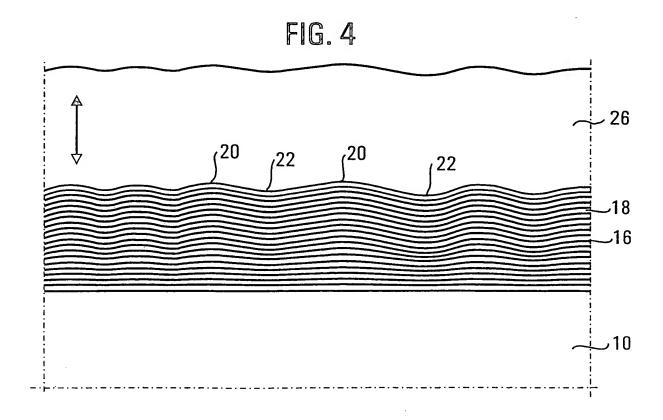


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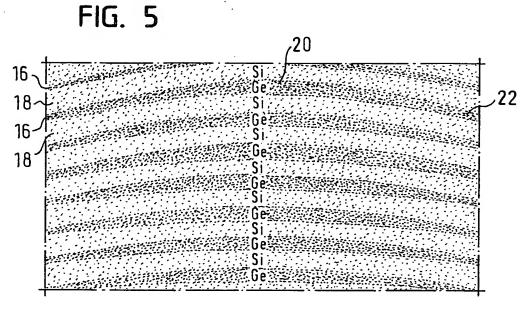


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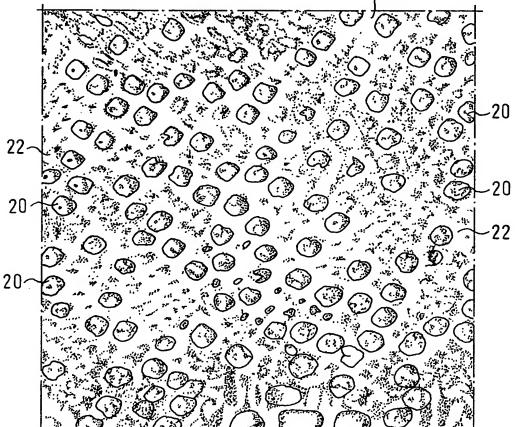
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## FIG. 6

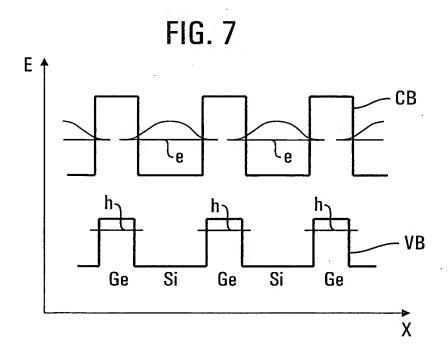


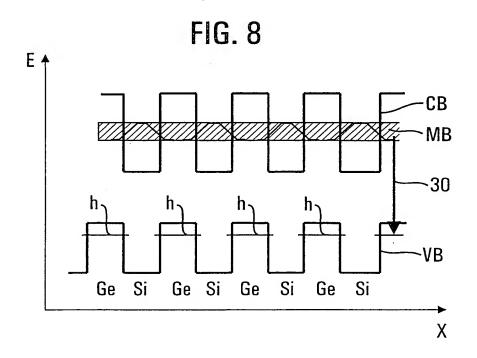
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Serial No.: 10/723,285 Inventors: Werner et al. Filed: November 25, 2003

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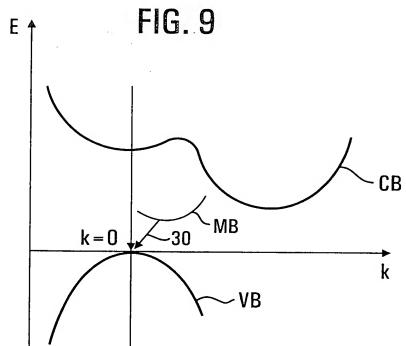
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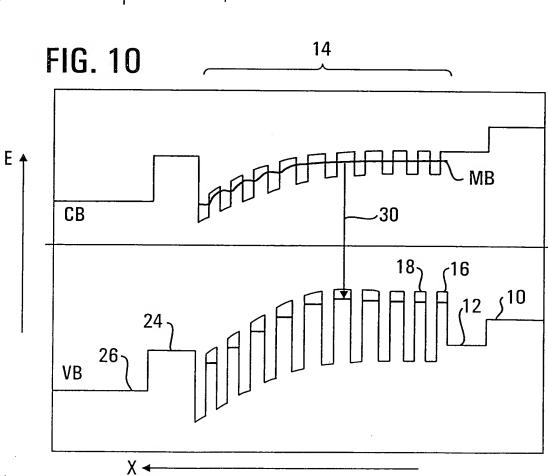
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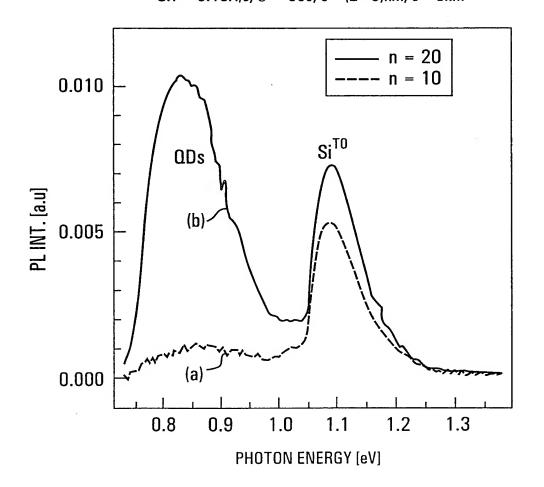
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FIG. 11

PL vs NUMBER OF LAYERS (n)  $T = 300 \text{ K} \\ E_{exc} = 2.54 \text{eV}, P = 5 \text{W/cm}^2 \\ \text{GR} = 0.15 \text{A/s}, \delta = 30 \text{s}, \text{s} = (2+3) \text{nm}, c = 5 \text{nm}$ 



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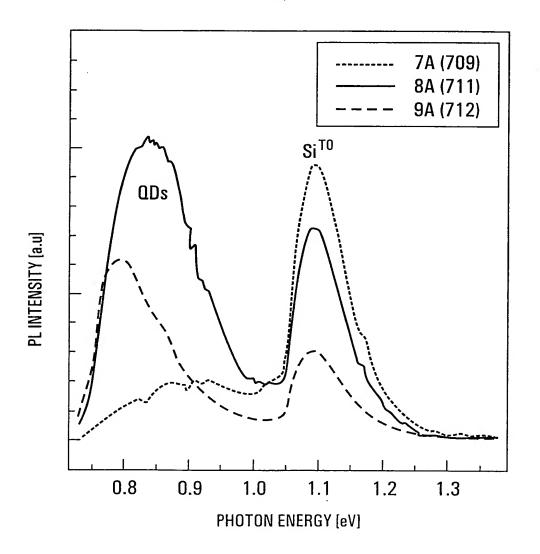
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FIG. 12

PL vs Ge THICKNESS (d) T = 300K  $E_{exc} = 2.54 eV, P = 5W/cm^2$  GR = 0.15 A/s, c = 5nm



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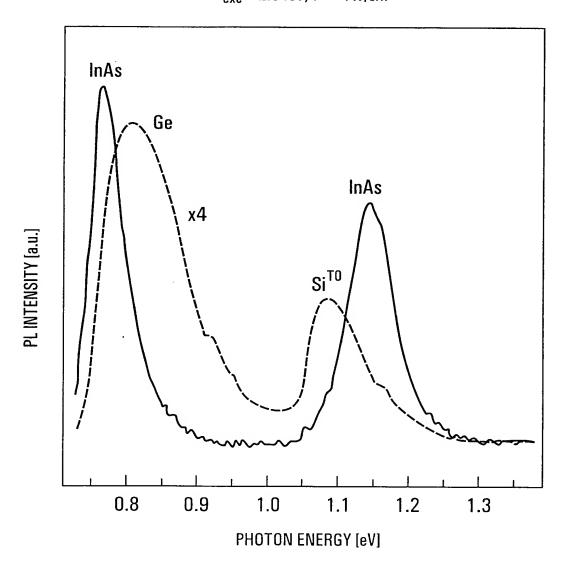
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FIG. 13

Ge-QDs vs InAs-QDs [LTLS] PL at T = 300K  $E_{exc}$  = 2.54eV, P = 1W/cm<sup>2</sup>

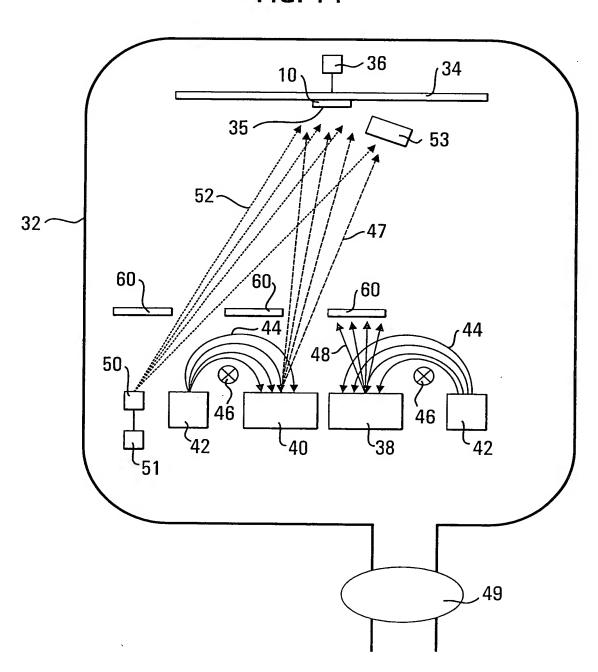


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FIG. 14



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